

UNIVERSITI MALAYSIA PERLIS

Peperiksaan Akhir Semester Pertama
Sidang Akademik 2020/2021

Disember 2020

DMT 231 – Analogue Electronics
[Elektronik Analog]

Masa: 3 jam

Please make sure that this question paper has **FOURTEEN (14)** printed pages including this front page before you start the examination.

*[Sila pastikan kertas soalan ini mengandungi **EMPAT BELAS (14)** muka surat yang bercetak termasuk muka hadapan sebelum anda memulakan peperiksaan ini.]*

This question paper has **TWO (2)** parts.

*[Kertas soalan ini mempunyai **DUA (2)** bahagian.]*

Part A : This part has **FOUR (4)** questions. Answer all questions (80 marks).
*[Bahagian A : Bahagian ini mengandungi **EMPAT (4)** soalan. Jawab semua soalan (80 markah).]*

Part B : This part has **TWO (2)** questions. Answer any **ONE (1)** question (20 marks).

*[Bahagian B : Bahagian ini mengandungi **DUA (2)** soalan. Jawab mana-mana **SATU (1)** soalan (20 markah).]*

Each question contributes **TWENTY (20)** marks.

*[Setiap soalan menyumbang **DUA PULUH (20)** markah.]*

List of equation is given in **Appendix**.

*[Senarai persamaan-persamaan diberikan pada **Lampiran**.]*

Part A*[Bahagian A]***Answer all questions.***[Jawab semua soalan.]***Question 1***[Soalan 1]*

- (a) State **TWO (2)** conditions for Bipolar Junction Transistor (BJT) as amplifying device.

[Nyatakan DUA (2) keadaan untuk Transistor Simpangan Dwipolar (BJT) sebagai peranti penguat.]

(2 Marks/ Markah)

- (b) Identify $i_C = (\beta / 1 + \beta) * i_E$ by using these 2 parameters:

*[Kenalpasti $i_C = (\beta / 1 + \beta) * i_E$ dengan menggunakan 2 parameter ini:]*

$$i_E = i_B + i_C \quad ; \quad i_C = \beta i_B$$

(3 Marks/ Markah)

- (c) Referring to **Figure 1**.

[Merujuk Rajah 1.]

- (i) Write the equation for base current, I_B for the amplifier circuit.

[Tuliskan persamaan bagi arus tapak, I_B bagi litar penguat.]

(2 Marks/ Markah)

- (ii) Sketch the small-signal equivalent circuit for the circuit.

[Lakarkan litar setara isyarat-kecil untuk litar.]

(6 Marks/ Markah)

- (iii) Label the small-signal equivalent circuit in (c)(ii).

[Labelkan litar setara isyarat-kecil dalam (c)(ii).]

(2 Marks/ Markah)

- (iv) Write the equation for output voltage, v_o and input voltage, v_s .

[Tulis persamaan bagi voltan keluaran, v_o dan voltan masukan, v_s .]

(3 Marks/ Markah)

- (v) Write the equation for small signal voltage gain, A_v .

[Tulis persamaan bagi gandaan voltan isyarat kecil, A_v .]

(2 Marks/ Markah)

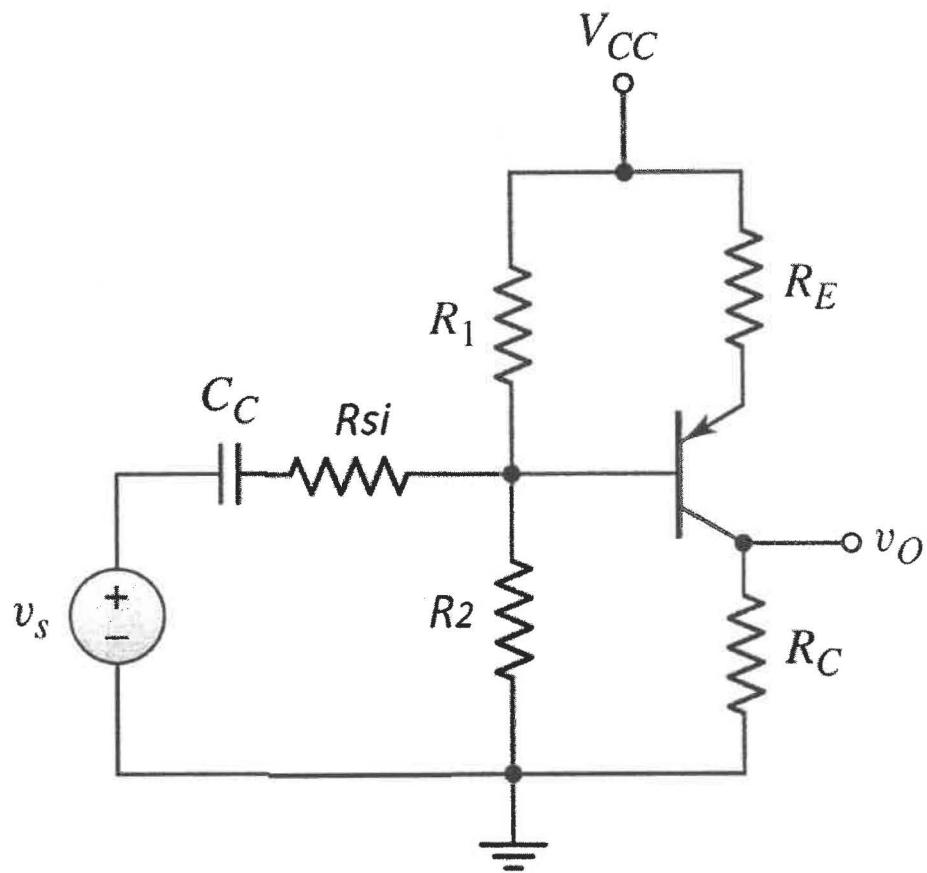


Figure 1
[Rajah 1]

Question 2
[Soalan 2]

- (a) Refer to **Figure 2**, identify the type of amplifier configuration for the amplifier circuit.

[Rujuk **Rajah 2**, kenalpasti jenis tatarajah penguat bagi litar penguat.]

(1 mark/ Markah)

- (b) For the amplifier circuit in **Figure 2**, assume the transistor parameters are $\beta = 75$, $V_{BE(on)} = 0.7$ V, $V_T = 26$ mV and $V_A = 80$ V. Evaluate:

[Untuk litar penguat dalam **Rajah 2**, andaikan parameter transistor adalah $\beta = 75$, $V_{BE(on)} = 0.7$ V, $V_T = 26$ mV dan $V_A = 80$ V. Nilaikan:]

- (i) base current, I_{BQ} .
 [arus tapak, I_{BQ} .]

(2 Marks/ Markah)

- (ii) collector current, I_{CQ} and emitter-collector voltage, V_{CEQ} .
 [arus pemungut, I_{CQ} dan voltan pemancar-pemungut, V_{CEQ} .]

(3 Marks/ Markah)

- (iii) transconductance, g_m .
 [transkonduktan, g_m .]

(2 Marks/ Markah)

- (iv) diffusion resistance, r_π and output resistance, r_o .
 [rintangan resapan, r_π dan rintangan keluaran, r_o .]

(2 Marks/ Markah)

- (c) Sketch and label small-signal equivalent circuit for circuit configuration shown in **Figure 2**.

[Lakarkan dan labelkan litar setara isyarat-kecil bagi tatarajah litar yang ditunjukkan dalam **Rajah 2**.]

(6 Marks/ Markah)

- (d) Evaluate small-signal voltage gain, A_v .
 [Nilaikan voltan gandaan isyarat-kecil, A_v .]

(4 Marks/ Markah)

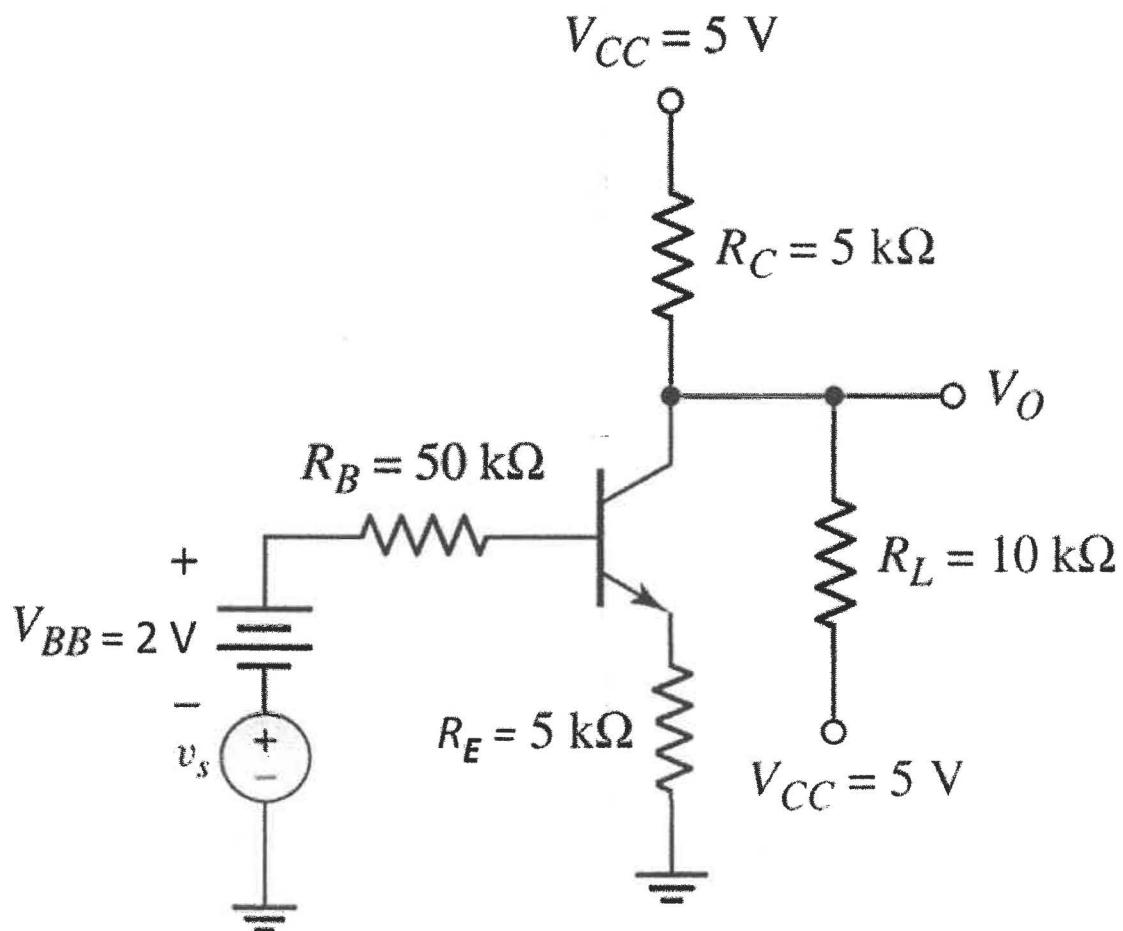


Figure 2
[Rajah 2]

Question 3
[Soalan 3]

- (a) State **THREE (3)** types of Metal Oxide Semiconductor Field Effect Transistor (MOSFET) amplifier.
[Nyatakan TIGA (3) jenis Separa Pengalir Oksida Logam Transistor Kesan Medan (MOSFET).]
 (3 Marks/ Markah)
- (b) State **TWO (2)** advantages of Field Effect Transistor (FET) device.
[Nyatakan DUA (2) kelebihan peranti Transistor Kesan Medan (FET).]
 (2 Marks/ Markah)
- (c) **Figure 3** show a MOSFET transistor with $K_n = 1 \text{ mA/V}^2$, $V_{TN} = 2 \text{ V}$, $\lambda = 0$, $R_L = 300 \text{ k}\Omega$, $R_2 = 200 \text{ k}\Omega$, $R_D = 3 \text{ k}\Omega$ and $R_s = 2 \text{ k}\Omega$.
[Rajah 3 menunjukkan satu transistor MOSFET dengan $K_n = 1 \text{ mA/V}^2$, $V_{TN} = 2 \text{ V}$ dan $\lambda = 0$, $R_L = 300 \text{ k}\Omega$, $R_2 = 200 \text{ k}\Omega$, $R_D = 3 \text{ k}\Omega$ and $R_s = 2 \text{ k}\Omega$.]
- (i) Evaluate gate voltage, V_G .
[Nilaikan voltan pintu, V_G .]
 (1 Mark/ Markah)
- (ii) Evaluate gate-source voltage, V_{GS} .
[Nilaikan voltan pintu sumber, V_{GS} .]
 (3 Marks/ Markah)
- (iii) Evaluate quiescent point (Q-point) values of I_{DQ} and V_{DSQ} .
[Nilaikan nilai-nilai titik sepi (titik-Q) bagi I_{DQ} dan V_{DSQ} .]
 (4 Marks/ Markah)
- (iv) Evaluate transconductance, g_m .
[Nilaikan transkonduktan, g_m .]
 (1 Mark/ Markah)
- (v) Sketch the small- signal equivalent circuit for the circuit.
[Lakarkan litar setara isyarat-kecil untuk litar.]
 (4 Marks/ Markah)
- (vi) Evaluate small-signal voltage gain, $A_v = v_o / v_i$
[Nilaikan gandaan voltan isyarat-kecil, $A_v = v_o / v_i$.]
 (2 Marks/ Markah)

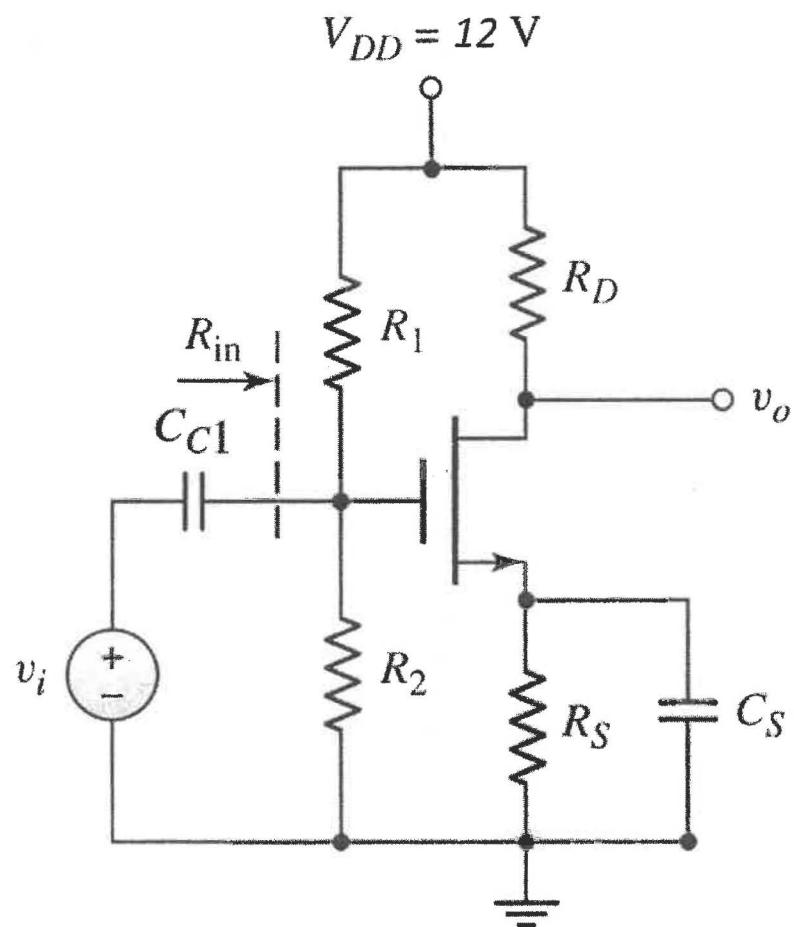


Figure 3
[Rajah 3]

Question 4*[Soalan 4]*

- (a) **Figure 4** shows a two-stage common-emitter amplifier in a cascade configuration with npn transistors. The circuit elements for transistor Q_1 and Q_2 are $\beta_1 = \beta_2 = 120$, $V_{BE(ON)} = 0.7$ V and $V_A = \infty$. Evaluate:

[Rajah 4 menunjukkan dua peringkat litar penguat pemancar-sepunya dalam satu lata tatarajah bersama transistor npn. Elemen-elemen untuk transistor Q_1 dan Q_2 adalah $\beta_1 = \beta_2 = 120$, $V_{BE(ON)} = 0.7$ V dan $V_A = \infty$. Nilaikan;]

- (i) Thevenin resistor and voltage, R_{TH} and V_{TH} for transistor Q_1 .
[Rintangan Thevenin, R_{TH} dan voltan Thevenin, V_{TH} untuk transistor Q_1 .]
(2 Marks/ Markah)
 - (ii) The quiescent current for transistor Q_1 , I_{BQ1} and I_{CQ1} .
[Arus sepi bagi transistor Q_1 , I_{BQ1} dan I_{CQ1} .]
(3 Marks/ Markah)
 - (iii) The quiescent current for transistor Q_2 , I_{BQ2} and I_{CQ2} .
[Arus sepi bagi transistor Q_2 , I_{BQ2} dan I_{CQ2} .]
(2 Marks/ Markah)
 - (iv) Diffusion resistance, $r_{\pi 1}$ and $r_{\pi 2}$.
[Rintangan resapan, $r_{\pi 1}$ dan $r_{\pi 2}$.]
(1 Mark/ Markah)
 - (v) Transconductance, g_{m1} and g_{m2}
[Transkonduktan, g_{m1} dan g_{m2} .]
(1 Mark/ Markah)
- (b) Sketch and label the AC equivalent circuit for multistage amplifier circuit shown in **Figure 4**.
[Lakar dan labelkan litar setara AC untuk litar penguat berbilang peringkat yang ditunjukkan dalam Rajah 4.]
(5 Marks/ Markah)
- (c) From answer in 4(b),
[Daripada jawapan dalam 4(b).]
- (i) Write the equation for output voltage, v_o and input voltage, v_s .
[Tulis persamaan bagi voltan keluaran, v_o dan voltan masukan, v_s .]
(4 Marks/ Markah)
 - (ii) Evaluate the small-signal voltage gain, A_v .
[Nilaikan gandaan voltan isyarat-kecil, A_v .]
(2 Marks/ Markah)

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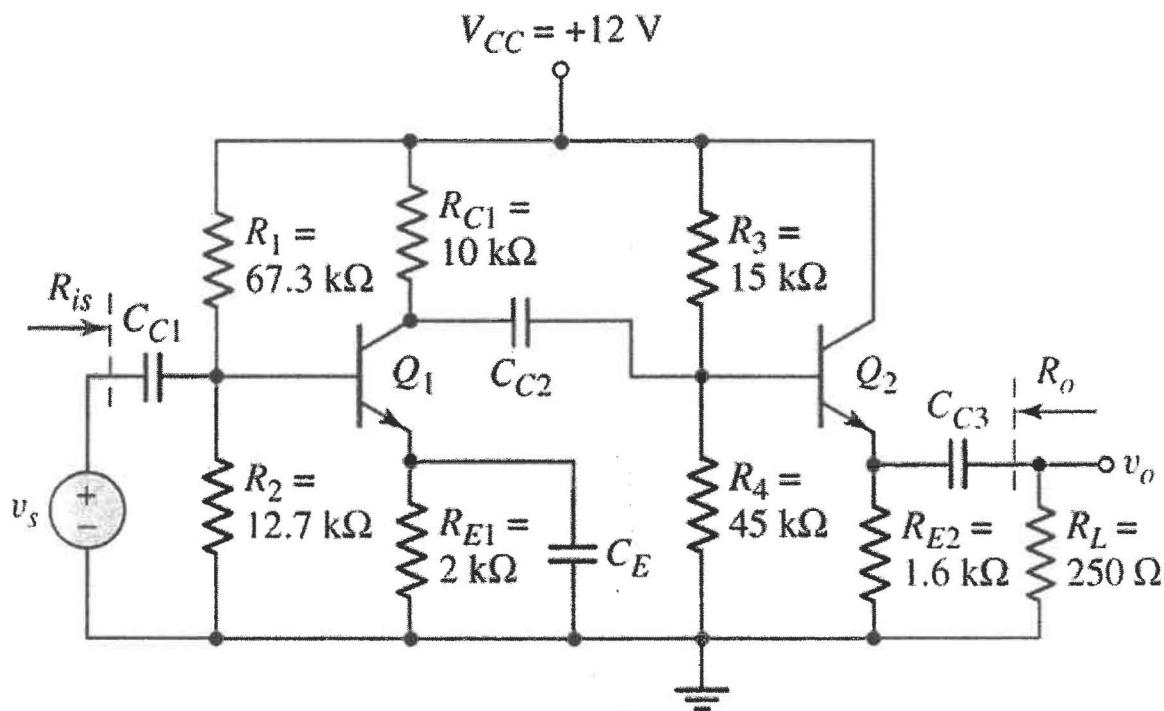


Figure 4
[Rajah 4]

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Part B*[Bahagian B]***Answer any ONE (1) question.***[Jawab mana-mana SATU (1) soalan.]***Question 5***[Soalan 5]*

- (a) Power amplifiers are generally classified into Class A, Class B, Class AB and Class C. Sketch and label collector current versus time for all class of power amplifiers.

[Penguat-penguat kuasa secara umum dikelaskan kepada Kelas A, Kelas B, Kelas AB dan Kelas C. Lakar dan labelkan arus pemungut melawan masa untuk kesemua kelas penguat-penguat kuasa.]

- (i) Class A and Class B amplifier

[Penguat kelas A dan kelas B.]

(4 Marks/ Markah)

- (ii) Class AB and Class C amplifier.

[Penguat kelas AB dan kelas C.]

(4 Marks/ Markah)

- (b) **Figure 5** shows an operation of Class AB power amplifier consists of complementary pair electronic devices. State the condition of transistor Q_n , Q_p , V_o and i_{Cn} when;

[Rajah 5 menunjukkan operasi Kelas AB penguat kuasa terdiri daripada peranti elektronik pasangan pelengkap. Nyatakan keadaan transistor Q_n , Q_p , V_o dan i_{Cn} apabila:]

- (i) $V_i = 0$.

[$V_i = 0$.]

(4 Marks/ Markah)

- (ii) V_i increase.

[V_i bertambah.]

(4 Marks/ Markah)

- (iii) V_i decrease.

[V_i berkurang.]

(4 Marks/ Markah)

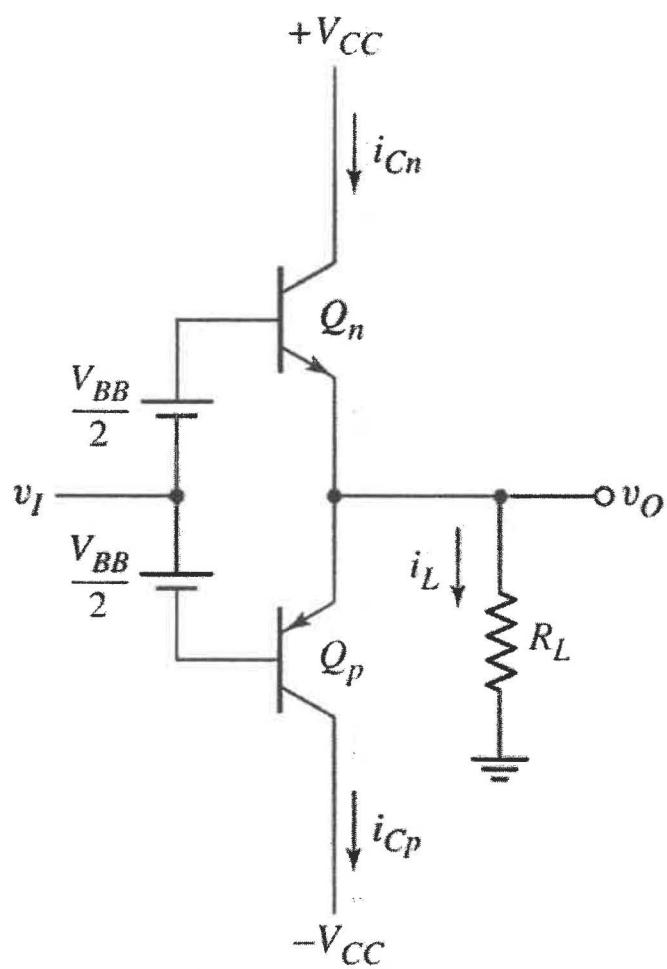


Figure 5
[Rajah 5]

Question 6
[Soalan 6]

- (a) JFET is three-terminal semiconductor device that can be used as electronically-controlled switches, amplifiers, or voltage-controlled resistors. Sketch and label:
[JFET adalah peranti semikonduktor tiga terminal yang boleh digunakan sebagai suis kawalan elektronik, penguat, atau voltan-kawalan perintang. Lakar dan labelkan:]
- (i) Junction Field Effect Transistor (JFET) symbol for both channels.
[Simpang Transistor Kesan Medan (JFET) simbol bagi kedua-dua saluran.]
 (4 Marks/ Markah)
- (ii) JFET bias circuit for self-bias circuit and voltage-divider bias circuit.
[litar pincang JFET bagi litar diri-pincang dan litar pembahagi-voltan pincang.]
 (4 Marks/ Markah)
- (b) The amplifier shown in **Figure 6(a)**, the transistor parameters are $IDSS = 12 \text{ mA}$, and $V_{GS(OFF)} = -3 \text{ V}$. The transfer characteristic curve is given in the **Figure 6(b)**.
[Penguat yang ditunjukkan dalam Rajah 6(a), parameter transistor adalah $IDSS = 12 \text{ mA}$ dan $V_{GS(OFF)} = -3 \text{ V}$. Lengkungan sifat pindahan diberi dalam Rajah 6(b).]
- (i) State the type of amplifier configuration for the amplifier circuit.
[Nyatakan jenis penguat tatarajah bagi litar penguat.]
 (2 Marks/ Markah)
- (ii) Calculate gate voltage, V_G .
[Kirakan voltan pintu, V_G .]
 (3 Marks/ Markah)
- (iii) Sketch a Direct Current (DC) load line and determine the Q-point for the circuit.
[Lakarkan garis beban Arus Terus (DC) dan tentukan titik-Q untuk litar.]
 (7 Marks/ Markah)

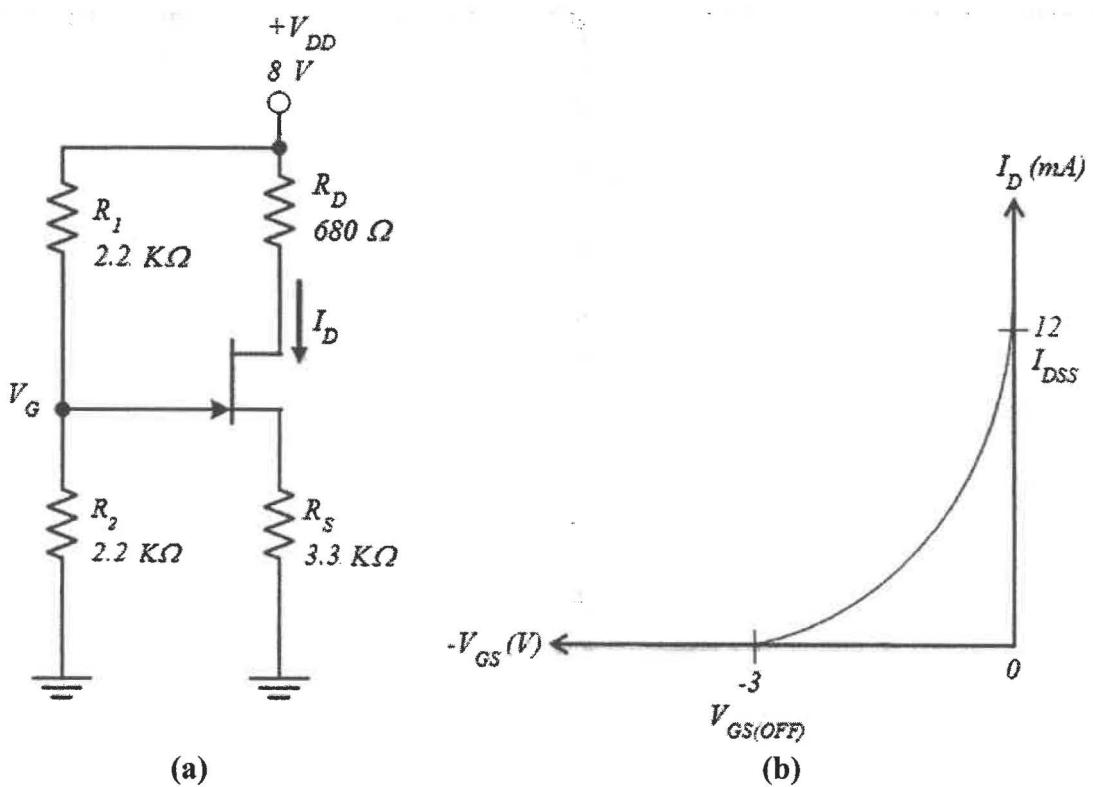


Figure 6
[Rajah 6]

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Appendix*[Lampiran]*

1.
$$g_m = \frac{I_{CQ}}{V_T}$$

2.
$$g_m = 2K_n(V_{GS} - V_{TN})$$

3.
$$g_m = \frac{2I_{DSS}}{|V_P|} \left(1 - \frac{V_{GS}}{V_P} \right)$$

4.
$$A_v = -g_m R_C \left(\frac{r_\pi}{r_\pi + R_D} \right)$$

5.
$$A_v = -g_m \left(\frac{R_1 \parallel R_2 \parallel r_\pi}{(R_1 \parallel R_2 \parallel r_\pi) + R_S} \right) (R_C \parallel r_o)$$

6.
$$A_v = -\frac{\beta R_C}{r_\pi + (1 + \beta) R_E} \left(\frac{R_i}{R_i + R_S} \right)$$

7.
$$A_v = \frac{(1 + \beta)(r_o \parallel R_E)}{r_\pi + (1 + \beta)(r_o \parallel R_E)} \left(\frac{R_i}{R_i + R_S} \right)$$

8.
$$A_v = g_m \left(\frac{R_C \parallel R_L}{R_S} \right) \left(\frac{r_\pi}{1 + \beta} \parallel R_E \parallel R_S \right)$$

9.
$$A_v = -g_m (r_o \parallel R_D)$$

10.
$$A_v = \frac{-g_m (r_o \parallel R_D \parallel R_L)}{1 + g_m R_S}$$

11.
$$A_v = -g_m (r_o \parallel R_D \parallel R_L) \left(\frac{R_i}{R_i + R_{Si}} \right)$$

12.
$$A_v = \frac{g_m (r_o \parallel R_S \parallel R_L)}{1 + g_m (r_o \parallel R_S \parallel R_L)} \left(\frac{R_i}{R_i + R_{Si}} \right)$$

13.
$$A_v = \frac{g_m (r_o \parallel R_D \parallel R_L)}{1 + g_m R_{Si}}$$

14.
$$A_v = -g_m (r_o \parallel R_D \parallel R_L)$$

15.
$$A_v = \frac{g_m (r_o \parallel R_S \parallel R_L)}{1 + g_m (r_o \parallel R_S \parallel R_L)}$$

16.
$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$

17.
$$I_D = K_N (V_{GS} - V_{TN})^2$$

18.
$$I_D = K_p (V_{SG} - V_{TP})^2$$

19.
$$V_{DS(sat)} = V_{GS} - V_{TN}$$

20.
$$V_{SD(sat)} = V_{SG} - V_{TP}$$